



DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} Max	I _D Max T _A = 25°C
	2.4Ω @ V _{GS} = 10V	510mA
60V	4.0Ω @ V _{GS} = 4V	390mA

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Up To 2kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- DC-DC Converters
- Power Management Functions
- Analog Switch

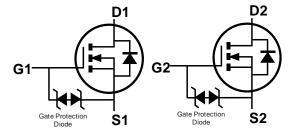
Mechanical Data

- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding
 Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (2)
- Weight: 0.015 grams (Approximate)

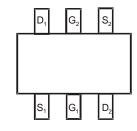




SOT26 Top View



Equivalent Circuit Per Element



Top View Internal Schematic

Ordering Information (Note 4)

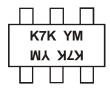
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Part Number	Case	Packaging
DMN601DMK-7	SOT26	3.000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.



Marking Information



K7K = Marking Code YM = Date Code Marking $Y \text{ or } \overline{Y} = Year (ex: S = 2005)$ M = Month (ex: 9 = September)

Date Code Key

Year	2005		2014	2015	2016	2017	2018	201	9 202	202	1 2022	2023	2024
Code	S		В	С	D	Е	F	G	Н	1	J	K	L
Month	Jan	Feb	Mar	Apr	Ma	y J	un	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5		6	7	8	9	0	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V_{DSS}	60	V		
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note C) (// 10\/)	Steady State	$T_A = +25$ °C $T_A = +70$ °C	ΙD	510 400	mA
Continuous Drain Current (Note 6) (V _{GS} = 10V)	t<10s	$T_A = +25$ °C $T_A = +70$ °C	I _D	580 470	mA
Continuous Drain Current (Note C) (1/ 4)/	Ι _D	390 300	mA		
Continuous Drain Current (Note 6) (V _{GS} = 4V	t<10s	$T_A = +25$ °C $T_A = +70$ °C	ПD	440 340	mA
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	850	mA		
Maximum Body Diode Continuous Current	Is	1.2	Α		

Thermal Characteristics

Characteristic		Symbol	Value	Units	
Total Power Dissipation (Note 5)		P _D	0.7	W	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	D	157	°C/W	
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{\theta JA}$	121		
Total Power Dissipation (Note 6)		P_{D}	0.98	W	
Thermal Decistores, Junction to Ambient (Note 6)	Steady State	<u> </u>	113	°C/W	
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{\theta JA}$	88		
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	26		
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C	

Notes:

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

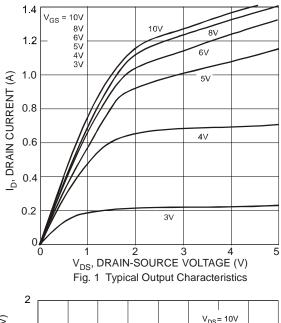
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	60			>	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Source Leakage	Igss	_	_	±10	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	1.0	1.6	2.5	V	$V_{DS} = 10V, I_{D} = 1mA$
Static Drain-Source On-Resistance	D	,	_	2.4	Ω	$V_{GS} = 10V, I_D = 200mA$
Static Dialit-Source Off-Resistance	R _{DS(ON)}		_	4.0	22	$V_{GS} = 4V, I_D = 200mA$
Forward Transfer Admittance	Y _{fs}	100	_	_	mS	$V_{DS} = 10V, I_D = 200mA$
Diode Forward Voltage	V_{SD}	0.5	_	1.4	V	$V_{GS} = 0V, I_S = 115mA$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	_	30	50	pF	05)/)/ 0)/
Output Capacitance	Coss	_	5	25	pF	$V_{DS} = 25V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	_	3	5.0	рF	1 - 1.000112
Gate Resistance	R_{g}	_	133	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge	Qg	_	304	_		1/ 451/1/ 401/
Gate-Source Charge	Q _{gs}	_	84	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$ $I_{D} = 250 \text{mA}$
Gate-Drain Charge	Q _{gd}	_	203	_		ID = 250MA
Turn-On Delay Time	t _{D(ON)}	_	3.9	_		
Turn-On Rise Time	t _R		3.4		nS	$V_{DS} = 30V, I_D = 0.2A,$
Turn-Off Delay Time	t _{D(OFF)}	_	15.7	_	115	$V_{GS} = 10V, R_G = 25\Omega, R_L = 150\Omega$
Turn-Off Fall Time	t _F	_	9.9	_		

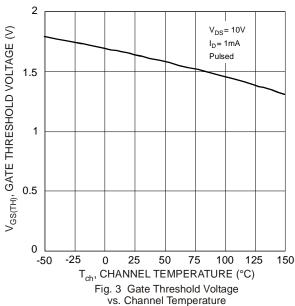
Notes:

^{7.} Short duration pulse test used to minimize self-heating effect.

^{8.} Guaranteed by design. Not subject to production testing.







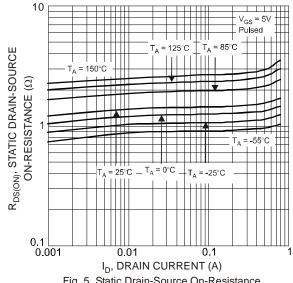
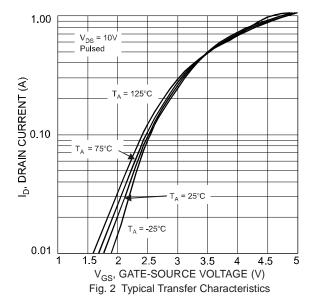


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current



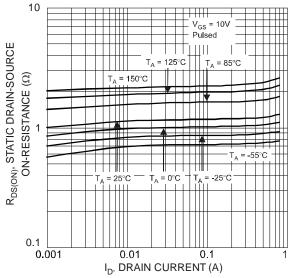


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

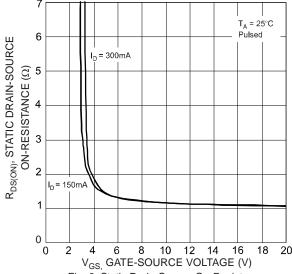


Fig. 6 Static Drain-Source On-Resistance vs. Gate-Source Voltage



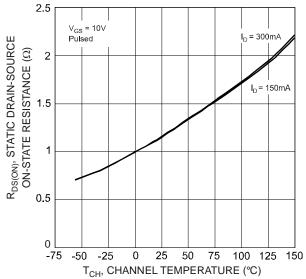


Fig. 7 Static Drain-Source On-State Resistance vs. Channel Temperature

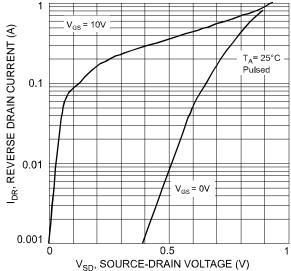


Fig. 9 Reverse Drain Current vs. Source-Drain Voltage

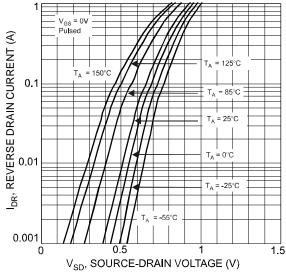


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

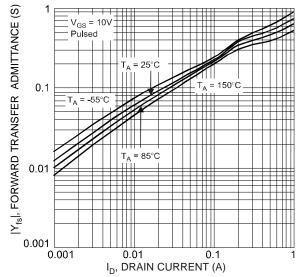


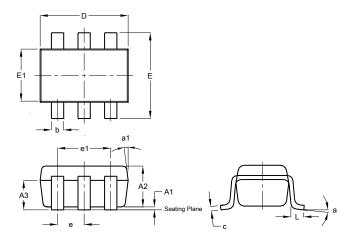
Fig.10 Forward Transfer Admittance vs. Drain Current



Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

SOT26

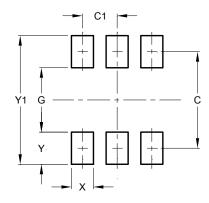


SOT26							
Dim	Min	Max	Тур				
A1	0.013	0.10	0.05				
A2	1.00	1.30	1.10				
A3	0.70	0.80	0.75				
b	0.35	0.50	0.38				
С	0.10	0.20	0.15				
D	2.90	3.10	3.00				
е		-	0.95				
e1	_	_	1.90				
Е	2.70	3.00	2.80				
E1	1.50	1.70	1.60				
L	0.35	0.55	0.40				
а	_		8°				
a1	_		7°				
All Dimensions in mm							

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

SOT26



Dimensions	Value (in mm)
С	2.40
C1	0.95
G	1.60
Х	0.55
Υ	0.80
Y1	3.20



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